

2SC1226, 2SC1226A

Silicon NPN Epitaxial Planar Type

Medium Power Amplifier

Complementary Pair with 2SA699, 2SA699A

■ Feature

- 5W output in complementary pair with 2SA699, 2SA699A

■ Absolute Maximum Ratings (Ta=25°C)

Item		Symbol	Value	Unit
Collector-base voltage	2SC1226	V_{CBO}	40	V
	2SC1226A		50	
Collector-emitter voltage	2SC1226	V_{CEO}	32	V
	2SC1226A		40	
Emitter-base voltage		V_{EBO}	5	V
Peak collector current		I_{CP}	3	A
Base current		I_B	0.6	A
Collector power dissipation ($T_c=25^\circ\text{C}$)		P_C	10	W
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature		T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

■ Electrical Characteristics (Tc=25°C)

Item		Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current		I_{CBO}	$V_{CB}=20\text{ V}, I_E=0$			1	μA
		I_{CEO}	$V_{CE}=12\text{ V}, I_B=0$			100	
Emitter cutoff current		I_{EBO}	$V_{EB}=5\text{ V}, I_C=0$			100	μA
Collector-base voltage	2SC1226	V_{CBO}	$I_C=1\text{ mA}, I_E=0$	40			V
	2SC1226A			50			
Collector-emitter voltage	2SC1226	V_{CEO}	$I_C=10\text{ mA}, I_B=0$	32			V
	2SC1226A			40			
DC current gain		h_{FE}^{*1}	$V_{CE}=5\text{ V}, I_C=1\text{ A}^{*2}$	50	120	220	
Transition frequency		f_T	$V_{CE}=5\text{ V}, I_C=0.5\text{ A}^{*2}$		150		MHz
Base-emitter saturation voltage		$V_{BE(sat)}$	$I_C=2\text{ A}, I_B=0.2\text{ A}^{*2}$			1.5	V
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C=2\text{ A}, I_B=0.2\text{ A}^{*2}$		0.4	1	V
Collector output capacitance		C_{ob}	$V_{CB}=5\text{ V}, I_E=0, f=1\text{ MHz}$		50		pF

*2 パルス測定

Life Classifications

Class	P	Q	R
Life	50~100	80~160	120~220

■ Package Dimensions

